

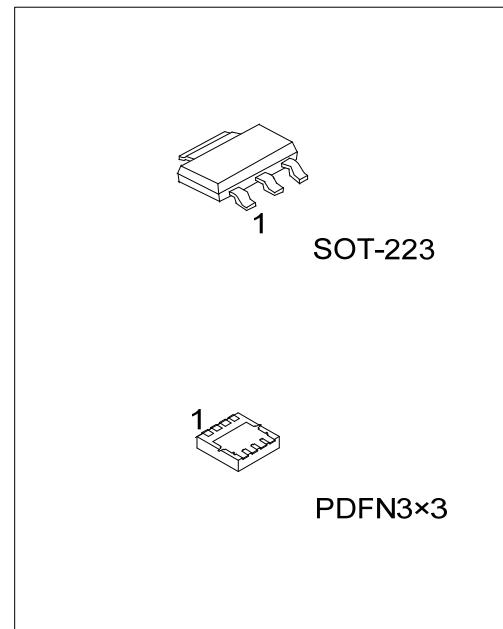
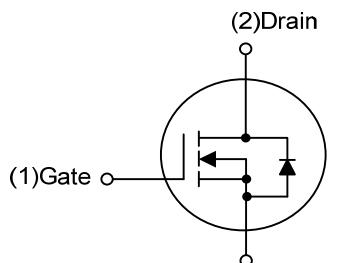
UTT16N15**POWER MOSFET****16A, 150V N-CHANNEL
POWER MOSFET****■ DESCRIPTION**

The UTC **UTT16N15** is a N-channel mode power MOSFET using UTC's advanced technology to provide customers with a minimum on-state resistance, low gate charge and high switching speed.

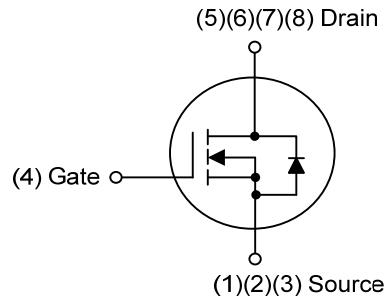
The UTC **UTT16N15** is suitable for high voltage synchronous rectifier and AC/DC converters, etc.

■ FEATURES

- * $R_{DS(ON)} \leq 150 \text{ m}\Omega @ V_{GS}=10\text{V}, I_D=4.0\text{A}$
- $R_{DS(ON)} \leq 170 \text{ m}\Omega @ V_{GS}=4.5\text{V}, I_D=4.0\text{A}$
- * High Switching Speed
- * High Cell Density Trench Technology

**■ SYMBOL**

SOT-223



PDFN3x3

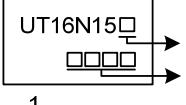
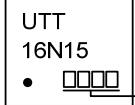
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment								Packing
Lead Free	Halogen Free		1	2	3	4	5	6	7	8	
UTT16N15L-AA3-R	UTT16N15G-AA3-R	SOT-223	G	D	S	-	-	-	-	-	Tape Reel
UTT16N15L-P3030-R	UTT16N15G-P3030-R	PDFN3x3	S	S	S	G	D	D	D	D	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

UTT16N15G-AA3-R 	(1)Packing Type (2)Package Type (3)Green Package	(1) R: Tape Reel (2) AA3: SOT-223, P3030: PDFN3x3 (3) G: Halogen Free and Lead Free, L: Lead Free
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■ MARKING

SOT-223	PDFN3x3
 <p>UT16N15 L: Lead Free G: Halogen Free Date Code 1</p>	 <p>UTT 16N15 • Date Code</p>

■ ABSOLUTE MAXIMUM RATING ($T_A = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER			SYMBOL	RATINGS	UNIT
Drain-Source Voltage			V_{DSS}	150	V
Gate-Source Voltage			V_{GSS}	± 20	V
Drain Current	Continuous	$T_A = 25^\circ\text{C}$	I_D	4	A
		$T_C = 25^\circ\text{C}$		16	A
	Pulsed (Note 2) ($T_C = 25^\circ\text{C}$)		I_{DM}	48	A
Avalanche Energy	Single Pulsed (Note 3)		E_{AS}	1.6	mJ
Peak Diode Recovery dv/dt (Note 4)			dv/dt	2.4	V/nS
Power Dissipation	SOT-223		P_D	2.5	W
	PDFN3x3			20	W
Junction Temperature			T_J	+150	$^\circ\text{C}$
Storage Temperature Range			T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. $L = 0.1\text{mH}$, $I_{AS} = 5.7\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25 \Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD} \leq 20\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	SOT-223	θ_{JA}	140	$^\circ\text{C/W}$
	PDFN3x3		130	$^\circ\text{C/W}$
Junction to Case	SOT-223	θ_{JC}	50	$^\circ\text{C/W}$
	PDFN3x3		6.25	$^\circ\text{C/W}$

Note: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

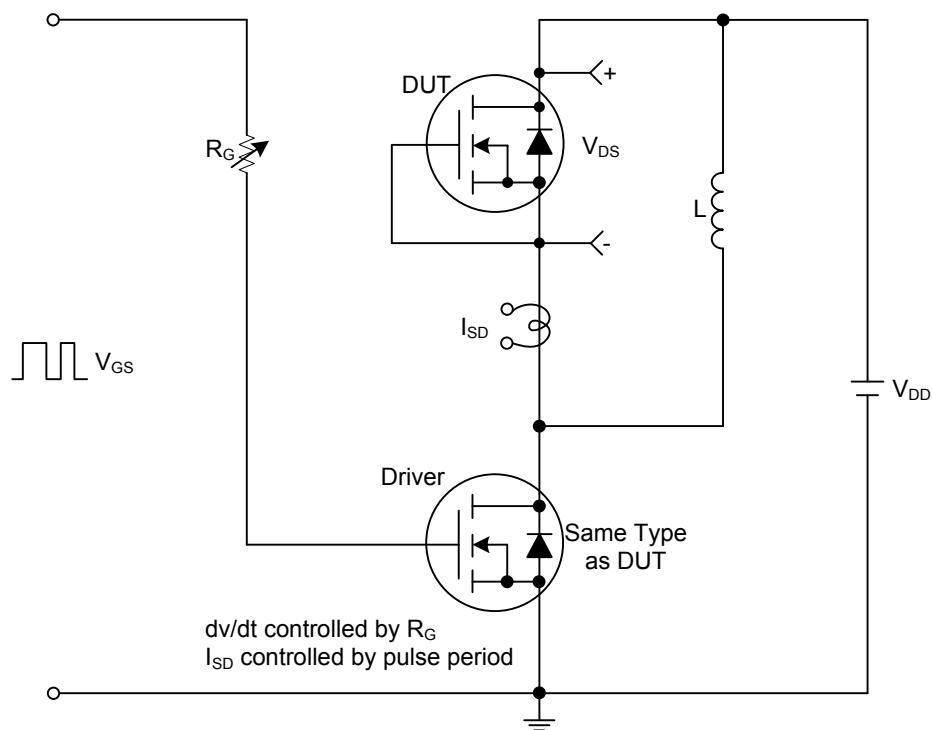
■ ELECTRICAL CHARACTERISTICS ($T_c = 25^\circ C$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=250\mu A, V_{GS}=0V$	150			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=150V, V_{GS}=0V$			1	μA
Gate-Source Leakage Current	Forward	$V_{GS}=+20V, V_{DS}=0V$			+100	nA
	Reverse	$V_{GS}=-20V, V_{DS}=0V$			-100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0		3.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=4.0A$			150	$m\Omega$
		$V_{GS}=4.5V, I_D=4.0A$			170	$m\Omega$
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	$V_{GS}=0V, V_{DS}=25V, f=1.0MHz$		900		pF
Output Capacitance	C_{OSS}			63		pF
Reverse Transfer Capacitance	C_{RSS}			40		pF
SWITCHING PARAMETERS						
Total Gate Charge (Note 1)	Q_G	$V_{DS}=120V, V_{GS}=10V, I_D=16A$ $I_G=1mA$ (Note 1, 2)		22		nC
Gate to Source Charge	Q_{GS}			3		nC
Gate to Drain Charge	Q_{GD}			4.5		nC
Turn-on Delay Time (Note 1)	$t_{D(ON)}$	$V_{DD}=30V, V_{GS}=10V, I_D=16A,$ $R_G=25\Omega$ (Note 1, 2)		8		ns
Rise Time	t_R			20		ns
Turn-off Delay Time	$t_{D(OFF)}$			85		ns
Fall-Time	t_F			48		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Body-Diode Continuous Current	I_S				16	A
Maximum Body-Diode Pulsed Current	I_{SM}				48	A
Drain-Source Diode Forward Voltage (Note 1)	V_{SD}	$I_S=16A, V_{GS}=0V$			1.4	V
Reverse Recovery Time (Note 1)	t_{rr}	$I_S=16A, V_{GS}=0V,$ $dI/dt=100A/\mu s$		66		nS
Reverse Recovery Charge	Q_{rr}			245		nC

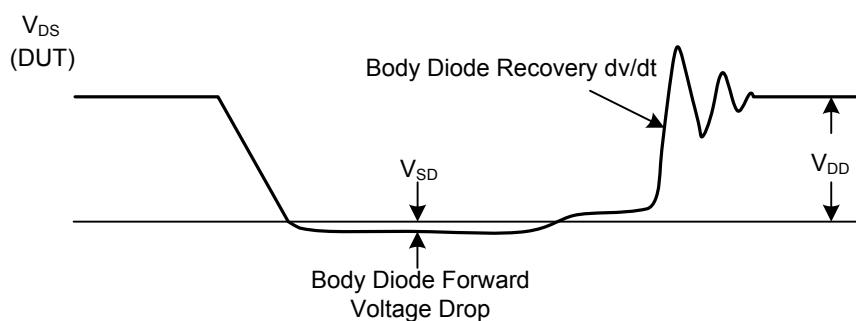
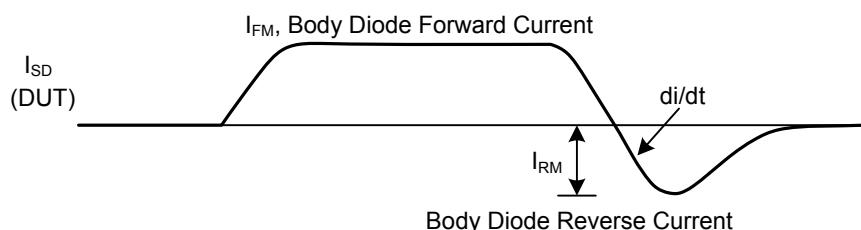
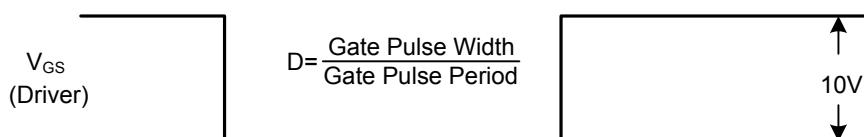
Notes: 1. Pulse Test : Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS



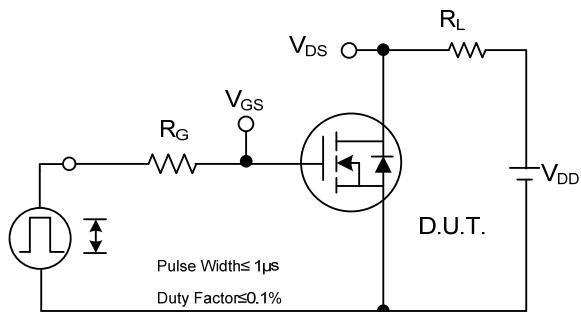
Peak Diode Recovery dV/dt Test Circuit



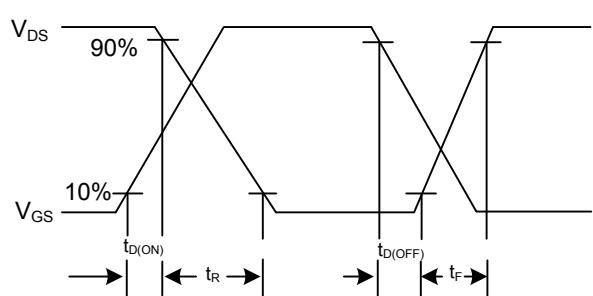
Peak Diode Recovery dV/dt Test Circuit and Waveforms

Peak Diode Recovery dV/dt Waveforms

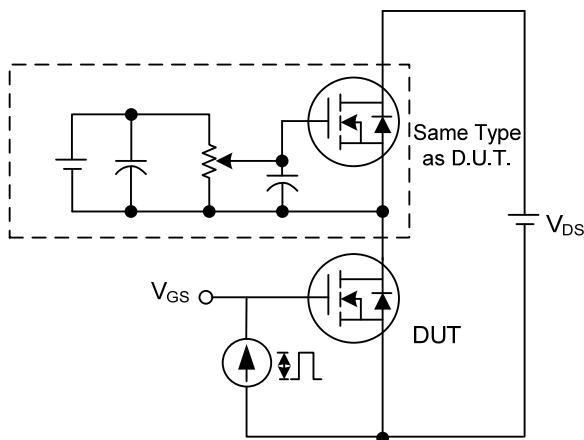
■ TEST CIRCUITS AND WAVEFORMS



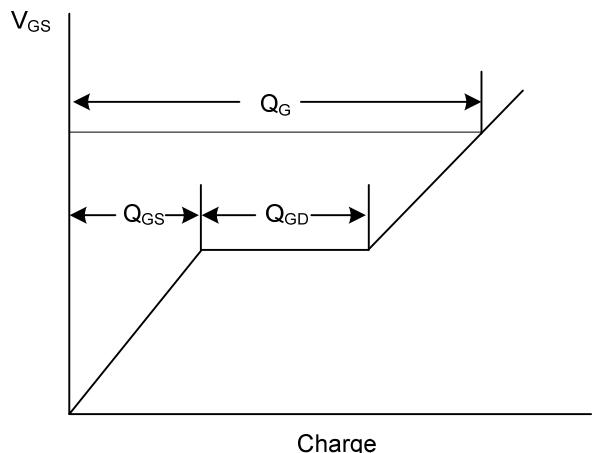
Switching Test Circuit



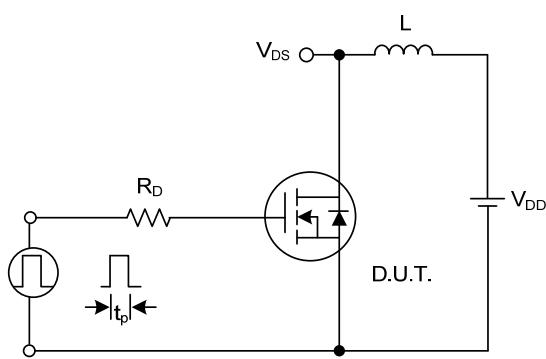
Switching Waveforms



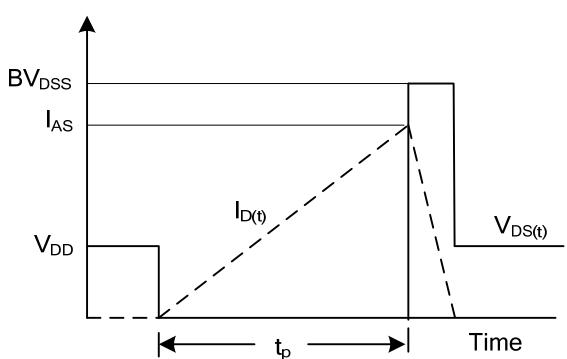
Gate Charge Test Circuit



Gate Charge Waveform

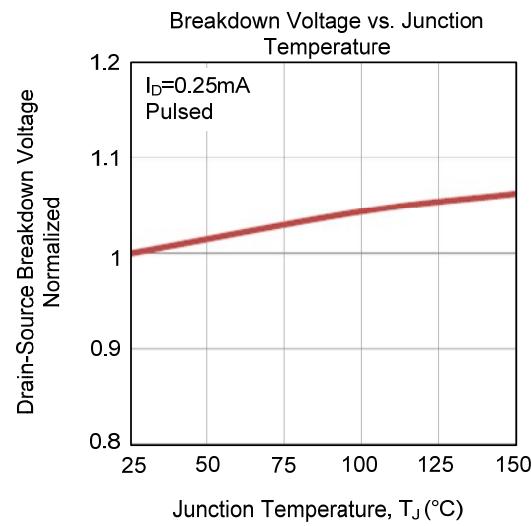
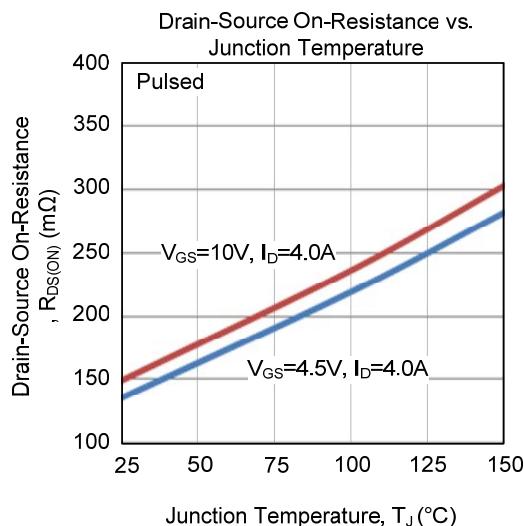
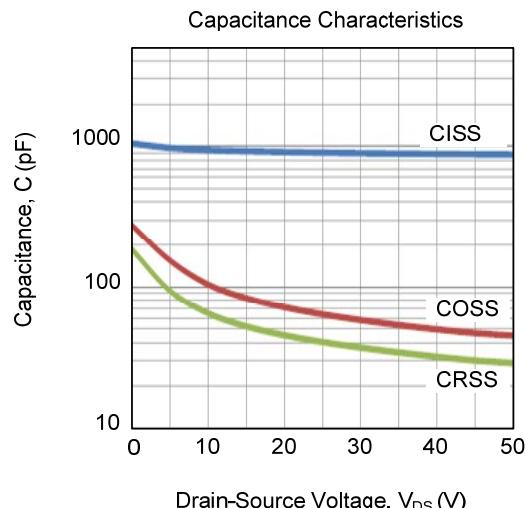
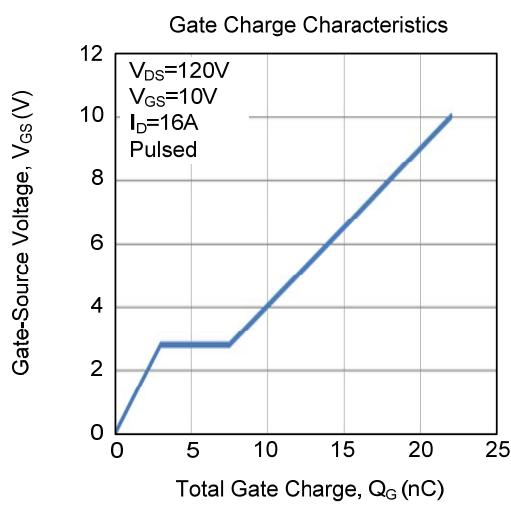
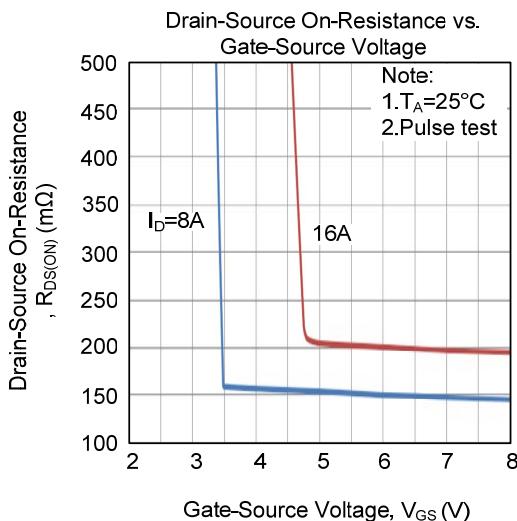
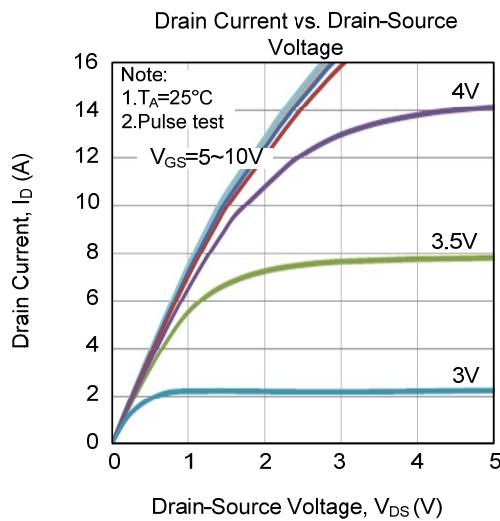


Unclamped Inductive Switching Test Circuit

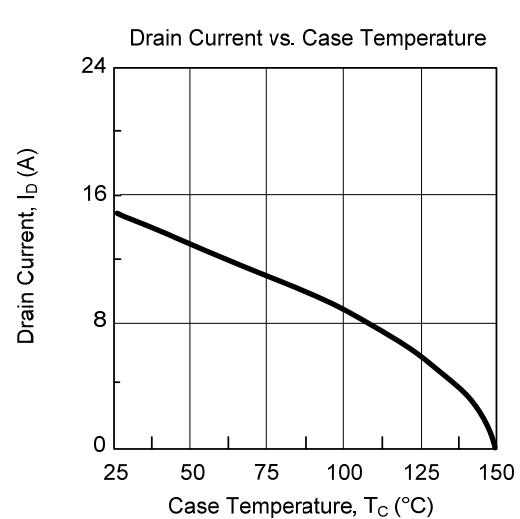
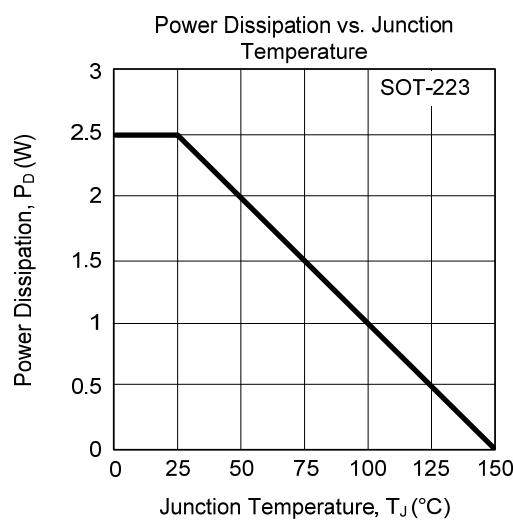
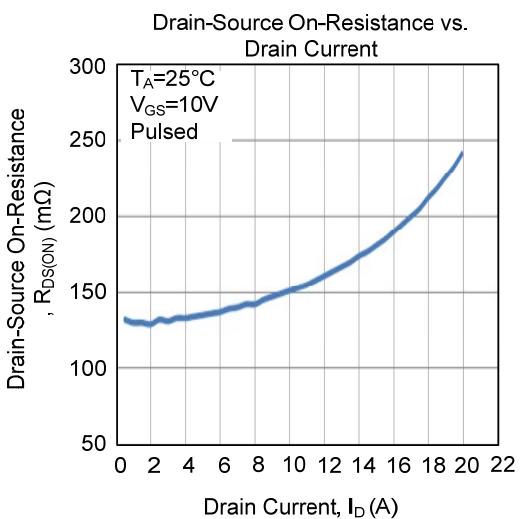
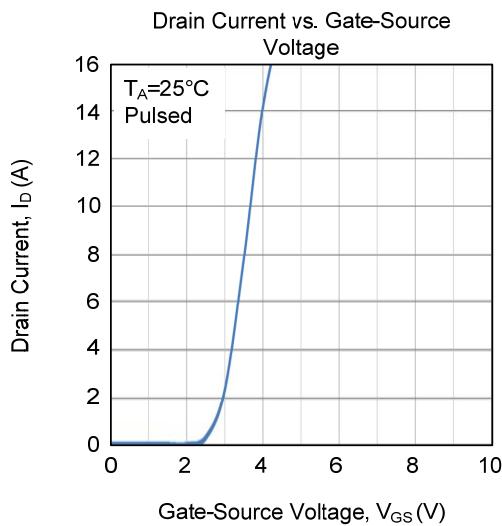
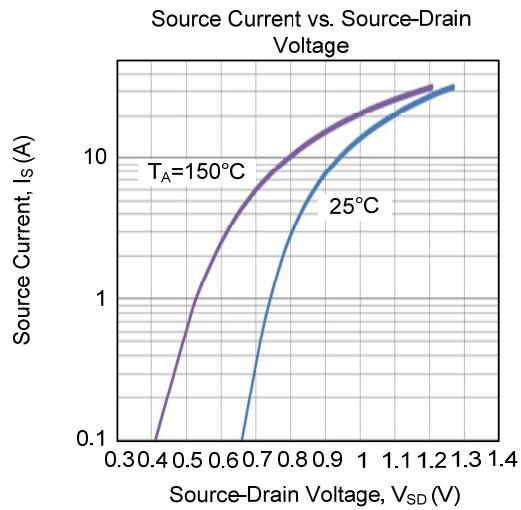
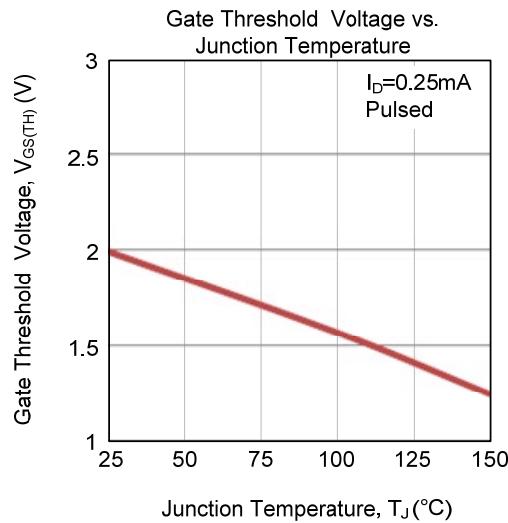


Unclamped Inductive Switching Waveforms

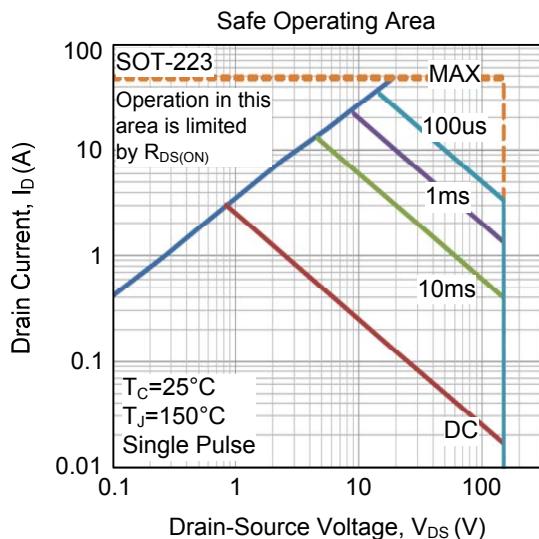
■ TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS (Cont.)



■ TYPICAL CHARACTERISTICS (Cont.)



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